

200206120

Abstract

In the case of the epitaxial growth according to the prior art, a number of strips often have to be produced in a plane in order to restore an area to be repaired. This leads to overlapping and misorientation of crystalline structures.

In the case of the method according to the invention, the strip is of such a width that no overlapping occurs, since the width is adapted to the contour of the area to be repaired.

figure 2